

PTO/SB/08A

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number	10/038,084
Filing Date	January 3, 2002
Confirmation Number	7363
First Named Inventor	Robert J. Falster
Group Art Unit	2811
Examiner Name	
Attorney Docket No.	MEMC 98-3052 (2512.2)

Sheet 1 of 10

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
A.M.	1	4,314,595		Yamamoto et al.	02/16/1982
	2	4,376,657		Nagasawa et al.	03/15/1983
	3	4,437,922		Bishoff et al.	03/20/1984
	4	4,505,759		O'Mara	03/19/1985
	5	4,548,654		Tobin	10/22/1985
	6	4,851,358		Huber	07/25/1989
	7	4,868,133		Huber	09/19/1989
	8	4,981,549		Yamashita et al.	01/01/1991
	9	5,189,500		Kusunoki	02/23/1993
	10	5,264,189		Yamashita et al.	11/30/1993
	11	5,327,007		Imura et al.	07/05/1994
	12	5,401,669		Falster et al.	03/28/1995
	13	5,403,406		Falster et al.	04/04/1995
	14	5,436,175		Nakato et al.	07/25/1995

Examiner Signature	ANH D. MAI	Date Considered	5/02/03
-----------------------	------------	--------------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

PTO/SB/08A INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/038,084
				Filing Date	January 3, 2002
				Confirmation Number	7363
				First Named Inventor	Robert J. Falster
				Group Art Unit	2811
				Examiner Name	
Sheet	2	of	10	Attorney Docket No.	MEMC 98-3052 (2512.2)

P.M.	15	5,445,975		Gardner et al.	08/29/1995
	16	5,474,020		Bell et al.	12/12/1995
	17	5,478,408		Mitani et al.	12/26/1995
	18	5,485,803		Habu	01/23/1996
	19	5,487,354		von Ammon et al.	01/30/1996
	20	5,502,010		Nadahara et al.	03/26/1996
	21	5,502,331		Inoue et al.	03/26/1996
	22	5,534,294		Kubota et al.	07/09/1996
	23	5,539,245		Imura et al.	07/23/1996
	24	5,561,316		Fellner	10/01/1996
	25	5,593,494		Falster	01/14/1997
	26	5,611,855		Wijaranakula	03/18/1997
	27	5,659,192		Sarma et al.	08/19/1997
	28	5,667,584		Takano et al.	09/16/1997
	29	5,674,756		Satoh et al.	10/07/1997
	30	5,704,973		Sakurada et al.	01/06/1998
	31	5,728,211		Takano et al.	03/17/1998
	32	5,738,942		Kubota et al.	04/14/1998
	33	5,788,763		Hayashi et al.	08/04/1998

Examiner Signature	ANH D. MAI	Date Considered	5/02/03
--------------------	------------	-----------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.



PTO/SB/08A INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/038,084
				Filing Date	January 3, 2002
				Confirmation Number	7363
				First Named Inventor	Robert J. Falster
				Group Art Unit	2811
				Examiner Name	
Sheet	3	of	10	Attorney Docket No.	MEMC 98-3052 (2512.2)

A.M	34	5,885,905		Nadahara et al.	03/23/1999
	35	5,939,770		Kageyama	08/17/1999
	36	5,944,889		Park et al.	08/31/1999
	37	5,954,873		Hourai et al.	09/21/1999
	38	5,968,262		Saishouji et al.	10/19/1999
	39	5,968,264		Iida et al.	10/19/1999
	40	6,045,610		Park et al.	04/04/2000
	41	6,236,104		Falster	05/22/2001

FOREIGN PATENT DOCUMENTS

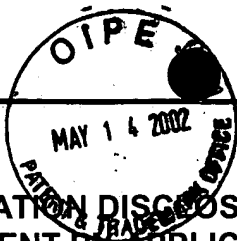
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ⁶
		Office	Number ⁴	Kind Code ² (if known)			
A.M	42	DE	3905626A1		Mitsubishi Kinzoku	08/31/1989	
	43	DE	4323964 A1		Tokyo Shibaura Electric Co.	01/20/1994	
	44	DE	4414947 A1		Wacker-Chemitronic	08/31/1995	
	45	DE	19806045 A1		Samsung Electronics	08/27/1998	
	46	EP	0504837 A2		Shin-Etsu Handota Co., Ltd	09/23/1992	
	47	EP	0503816 B1		Shin-Etsu Handota Co. Ltd	09/18/1992	
	48	EP	0536958 A1		Shin-Etsu Handotai Co. Ltd.	04/14/1993	

Examiner Signature	ANH D. MAI	Date Considered	5/02/03
-----------------------	------------	--------------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.



PTO/SB/08A INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10/038,084
				Filing Date	January 3, 2002
				Confirmation Number	7363
				First Named Inventor	Robert J. Falster
				Group Art Unit	2811
				Examiner Name	
Sheet	4	of	10	Attorney Docket No.	MEMC 98-3052 (2512.2)

A.M	49	EP	0716168 A1		Shin-Etsu Handotai Co. Ltd.	06/12/1996	
	50	EP	0799913		Leybold AG	12/08/1998	
	51	EP	0915502		Shin-Etsu Handotao K.K.	05/12/1999	
	52	EP	0954018		Sumitomo Metal Industries Ltd.	11/03/1999	
	53	EP	0962556 A1		Shin-Etsu Handotai Co. Ltd.	12/08/1999	
	54	GB	2182262		Sony Corporation	05/13/1986	
	55	JP	59119822 (Abstract)		Fujitsu Ltd.	07/11/1984	
	56	JP	2-32535		Kyushu Electronic Metal et al.	02/02/1988	X
	57	JP	1-242500		Mitsubishi Kinzoku Kabushiki Kaisha	09/27/1989	X
	58	JP	2180789 (Abstract only)		Kawasaki Steel Corp.	07/13/1990	
	59	JP	3-9078		Mitsubishi Metal K.K. Tokyo	02/07/1991	
	60	JP	3-185831		Komatsu Electronic Metals Co.	08/13/1991	X
	61	JP	4108682 (Abstract only)		Fuji Electric Co., Ltd.	04/09/1992	
	62	JP	4-294540		Nippon Steel Corp.	10/19/1992	X
	63	JP	5-155700 A		Nippon Steel Corp.	06/22/1993	
	64	JP	8-330316		Sumitomo Sitix Ltd.	05/31/1995	
	65	JP	7-201874 A		NEC Corp.	08/04/1995	

Examiner Signature	ANH D. MAI	Date Considered	5/02/03
-----------------------	------------	--------------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

PTO/SB/08A

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number 10/038,084

Filing Date January 3, 2002

Confirmation Number 7363

First Named Inventor Robert J. Falster

Group Art Unit 2811

Examiner Name

Sheet

5

of

10

Attorney Docket No.

MEMC 98-3052 (2512.2)

A.M	66	JP	7321120 (Abstract only)		Komatsu Electron Metals Co. Ltd.	12/08/1995	
	67	JP	7335657 (Abstract only)		Komatsu Electron Metals Co. Ltd.	12/22/1995	
	68	JP	8045944 (Abstract only)		Sumitomo Sitix Corp.	02/16/1996	
	69	JP	8045947 (Abstract only)		Nippon Steel Corp.	02/16/1996	
	70	JP	8/045945		Mitsubishi Materials Corp.	02/16/1996	
	71	JP	8/268794		Sumitomo Sitix, Ltd.	10/15/1996	
	72	JP	8-293589 (Abstract)		Hitachi Ltd.	11/05/1996	
	73	JP	9/199416		Sumitomo Sitix Ltd.	07/31/1997	
	74	JP	9/202690		Shinetsu Semi-Conductor	08/05/1997	
	75	JP	9-326396 (Abstract)		Hitachi Ltd.	12/06/1997	
	76	JP	11-150119		Sumitomo Sitix Corp.	06/02/1999	
	77	JP	11-067781 A		Sumitomo Metal Ind. Ltd.	03/0/1999	
	78	JP	11-157995 A		Sumitomo Sitix Corp.	06/15/1999	
	79	JP	11-180800 A		Shin Etsu Handotai Co. Ltd.	07/06/1999	
	80	JP	11-189495 A		Sumitomo Metal Ind. Ltd.	07/13/1999	
	81	JP	11-199386 A		Shin Etsu Handotai Co. Ltd.	07/27/1999	

Examiner
Signature

ANH D. MAI

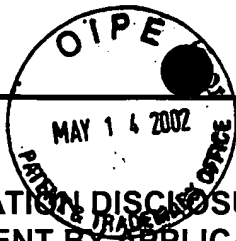
Date
Considered

5/02/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.



PTO/SB/08A

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number	10/038,084
Filing Date	January 3, 2002
Confirmation Number	7363
First Named Inventor	Robert J. Falster
Group Art Unit	2811
Examiner Name	
Attorney Docket No.	MEMC 98-3052 (2512.2)

Sheet 6 of 10

A.M	82	JP	11-199387 A	Shin Etsu Handotai Co. Ltd.	07/27/1999
	83	WO	97/26393	Shin Etsu Handotai Co. Ltd.	07/24/1997
	84	WO	98/38675	MEMC Electronic Materials, Inc.	09/03/1998
	85	WO	98/45507	MEMC Electronic Materials, Inc.	10/15/1998
	86	WO	98/45508	MEMC Electronic Materials, Inc.	10/15/1998
	87	WO	98/45509	MEMC Electronic Materials, Inc.	10/15/1998
	88	WO	98/45510	MEMC Electronic Materials, Inc.	10/15/1998

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

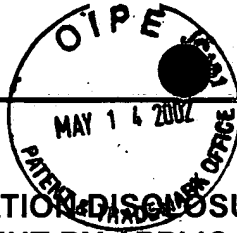
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
A.M	89	ABE, T., "Innovated Silicon Crystal Growth and Wafering Technologies" Electrochemical Society Proceedings, vol. 97, No. 3, pp. 123-133. (No Month).	
	90	ABE, T., et al., "Defect-Free Surfaces of Bulk Wafers by Combination of RTA and Crystal Growth Conditions" (publication information unknown) (No Month/No Year).	
	91	CHIOU, H.D., et al., "Gettering of Bonded Soi Layers", Proceedings of the International Symposium on Silicon-On-Insulator Technology and Devices, pp. 416-423	
	92	CHIOU, HERING-DER, "The Effects of Preheatings on Axial Oxygen Precipitation Uniformity in Czochralski Silicon Crystals", J. Electrochem. Soc., vol. 139, No. 6, Jun. 1992.	
	93	de KOCK, A.J.R., et al., "The Effect of Doping on the Formation of Swirl Defects in Dislocation-Free Czochralski-Grown Silicon Crystals", Journal of Crystal Growth, Vol. 49, pp. 718-734, 1980.	

Examiner Signature	ANH D. MAI	Date Considered	5/02/03
--------------------	------------	-----------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.



PTO/SB/08A INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	09/737,715
				Filing Date	December 15, 2000
				Confirmation Number	9249
				First Named Inventor	Robert J. Falster
				Group Art Unit	
				Examiner Name	
Sheet	7	of	10	Attorney Docket No.	MEMC 98-3051 (2512.1)

A.M	94	DORNBERGER, E., et al., "The Dependence Ring Like Distributed Stacking Faults on the Axial Temperature Gradient of Growing Czochralski Silicon Crystals", Electrochemical Society Proceedings, vol. 95-4, (May 1995) pp. 294-305	
	95	DORNBERGER, E., et al., "Simulation of Grown-In Voids in Czochralski Silicon Crystals", Electrochemical Society Proceedings, Volume 97, No. 22, pp. 40-49	
	96	DORNBERGER, E., et al., "Simulation of Non-Uniform Grown-In Void Distributions in Czochralski Silicon Crystals", Electrochemical Society Proceedings, Vol. 98, Vol. 1, pp. 490-503	
	97	DORNBERGER, E., et al., "The Impact of Dwell Time Above 900°C During Crystal Growth on the Gate Oxide Integrity of Silicon Wafers", Electrochemical Society Proceedings, Volume 96, No. 13, pp. 140-151.	
	98	EIDENZON, A.M., et al., "Defect-free Silicon Crystals Grown by The Czochralski Technique", Inorganic Materials, Vol. 33, No. 3 (1977) pp.219-225	
	99	EIDENZON, A.M., et al., "Influence of Growth Rate on Swirl Defects in Large Dislocation-Free Crystals of Silicon Grown by the Czochralski Method", Sov. Phys. Crystallogr., Vol. 30, No. 5 (1985) pp.576-580, American Institute of Physics	
	100	FALSTER, R., et al., "The Engineering of Silicon Wafer Material Properties Through Vacancy Concentration Profile Control and the Achievement of Ideal Oxygen Precipitation Behavior", Mat. Res. Soc. Symp. Proc. vol. 510, pp. 27-35, 1998 (No Month).	
	101	FALSTER, R., et al., "Intrinsic Point-Defects and Reactions in the Growth of Large Silicon Crystals", Electrochemical Society Proceedings, vol. 98-1, pp. 468-489	
	102	HARA, A., et al. "Enhancement of Oxygen Precipitation in Quenched Czochralski Silicon Crystals" Journal of Applied Phys. vol. 66 (1989) pp. 3958-3960 (Oct. 1989).	
	103	HAWKINS, G.A., et al., "Effect of Rapid Thermal Processing on Oxygen Precipitation in Silicon", Mat. Res. Soc. Symp. Proc., Vol. 104, pp. 197-200, 1988.	
	104	HAWKINS, G.A., et al., "The Effect of Rapid Thermal Annealing on the Precipitation of Oxygen in Silicon", J. Appl. Phys., Vol. 65, No. 9, pp. 3644-3654, 1989	

Examiner Signature	ANH D. MAI	Date Considered	5/02/03
--------------------	------------	-----------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.



PTO/SB/08A INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	09/737,715
				Filing Date	December 15, 2000
				Confirmation Number	9249
				First Named Inventor	Robert J. Falster
				Group Art Unit	
				Examiner Name	
Sheet	8	of	10	Attorney Docket No.	MEMC 98-3051 (2512.1)

A.M	105	HOURAI, M., et al. "Growth Parameters Determining the Type of Grown-In Defects in Czochralski Silicon Crystals", Materials Science Forum, Vols. 196-201 (1995) pp. 1713-1718	
	106	JACOB, M., et al. "Influence of RTP on Vacancy Concentrations", Mat. Res. Soc. Symp. Proc. vol. 490, pp. 129-134, 1998. (No Month).	
	107	JACOB, et al., "Determination of Vacancy Concentrations in the Bulk of Silicon Wafers by Platinum Diffusion Experiments", J. Appl. Phys., Vol. 82, No. 1 (1997), pp. 182-191.	
	108	KISSINGER, G., et al., "A Method for Studying the Grown-In Defect Density Spectra in Czochralski Silicon Wafers", J. Electrochem. Soc., Vol. 144, No. 4, pp. 1447-1456, 1997.	
	109	MULESTAGNO, L., et al., "Gettering of Copper in Bonded Silicon Wafers", Electrochemical Society Proceedings, Vol. 96, No. 3, pp. 176-182.	
	110	NADAHARA, et al., "Hydrogen Annealed Silicon Wafer", <i>Solid State Phenomena</i> , Vols. 57-58, pp. 19-26, 1997	
	111	NAKAMURA, KOZO, et al., "Formation Process of Grown-In Defects in Czochralski Grown Silicon Crystals", Journal of Crystal Growth, Vol. 180, pp. 61-72, 1997.	
	112	PAGANI, M., et al. "Spatial variations on oxygen precipitation in silicon after high temperature rapid thermal annealing", Appl. Phys. Lett., vol. 70, No. 12, pp. 1572-1574, 1997. (Mar. 1997).	
	113	PARK, J.G., et al., "Effect of Crystal Defects on Device Characteristics", <i>Proceedings of the Symposium on Crystalline Defects and Contamination: Their Impact And Control In Device Manufacturing II</i> , Proceed. Vol. 97-22 (1997), pp.173-195	
	114	PUZANOV, N.I. et al. "Modelling Microdefect Distribution In Dislocation-Free Si Crystals Grown From The Melt"; Journal of Crystal Growth 178 (1997) pp. 468-478	
	115	PUZANOV, N.I. et al. "Formation Of The Bands Of Anomalous Oxygen Precipitation In Czochralski-grown Si Crystals", Journal of Crystal Growth 137 (1994) pp. 642-652	
	116	PUZANOV, N.I. et al. "The Role Of Intrinsic Point Defects In The Formation Of Oxygen Precipitation Centers In Dislocation-Free Silicon"; Crystallography Reports; Vol. 41; No. 1(1996) pp. 134-141	

Examiner Signature	ANH D. MAI	Date Considered	5/02/03
--------------------	------------	-----------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.



PTO/SB/08A

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number	09/737,715
Filing Date	December 15, 2000
Confirmation Number	9249
First Named Inventor	Robert J. Falster
Group Art Unit	
Examiner Name	

Sheet	9	of	10	Attorney Docket No.	MEMC 98-3051 (2512.1)
-------	---	----	----	---------------------	-----------------------

A.M	117	PUZANOV, N.I. et al. "Harmful Microdefects In The Seed-End Portion Of Large-Diameter Silicon Ingots", Inorganic Materials, Vol. 33, No. 8 (1997) pp. 765-769	
	118	PUZANOV, N.I., et al., "Role of Vacancies in the Nucleation of Ringlike-patterned Oxidation-induced Stacking Faults in Melt-grown Silicon Crystals", Inorganic Materials, Vol. 34, No 4 (1998) pp.307-314	
	119	SHIMIZU, H., et al. "Effects of Surface Defects (COPs) On Isolation Leakage and Gate Oxide Integrity in MOS Large-Scale-Integrated-Circuit Devices and Cost Effective p-1p-Epitaxial Wafers", <i>Electrochemical Society Proceedings</i> , Vol. 99, No. 1, pp. 315-323 (from a presentation on or about May 3, 1999)	
	120	SHIMIZU, H., et al., "Excellence of Gate Oxide Integrity in Metal-Oxide-Semiconductor Large-Scale-Integrated Circuits based on P-/P-Thin-Film Epitaxial Silicon Wafers", <i>Jpn. J. Appl. Phys.</i> , Vol. 36, pp. 2565-2570 Part 1, No. 5A, 1997	
	121	SHIMURA, F., "Semiconductor Silicon Crystal Technology" Academic Press, Inc., San Diego, CA (1989) pp. 360-377. (No Month).	
	122	SINNO, T., et al., "On the Dynamics of the Oxidation-Induced Stacking-Fault Ring in as-grown Czochralski silicon crystals", <i>Applied Physics Letters</i> , Vol. 70, No. 17, pp. 2250-2252, 1997.	
	123	SINNO, T., et al., "Point Defect Dynamics and the Oxidation-Induced Stacking-Fault Ring in Czochralski-Grown Silicon Crystals", <i>J. Electrochem. Soc.</i> , Vol. 145, No. 1, pp. 302-318, 1998.	
	124	TAN, T. Y., "Point Defects, Diffusion Processes, and Swirl Defect Formation in Silicon", <i>Appl. Phys. A.</i> , Vol. 37, pp. 1-17, 1985.	
	125	VANHELLEMONT, J., et al., "Defects in As-Grown Silicon and Their Evolution During Heat Treatments", <i>Materials Science Forum</i> , Vols. 258-263, pp. 341-346, 1997.	
	126	VON AMMON et al. "The Dependence of Bulk Defects on the Axial Temperature Gradient of Silicon Crystals During Czochralski Growth" <i>Journal of Crystal Growth</i> , Vol. 151 (1995) pp. 273-277.	
	127	VORONKOV, "The Mechanism of Swirl Defects Formation in Silicon", <i>Journal of Crystal Growth</i> , Vol. 59, pp. 625-643, 1982.	
	128	VORONKOV, V., et al., "Behavior and Effects of Intrinsic Point Defects in the Growth of Large Silicon Crystals" <i>Electrochemical Society Proceedings</i> , vol. 97-22, (Aug. 1997), pp. 3-17	

Examiner
Signature

ANH D. MAI

Date
Considered

5/02/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

PTO/SB/08A

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number	09/737,715
Filing Date	December 15, 2000
Confirmation Number	9249
First Named Inventor	Robert J. Falster
Group Art Unit	
Examiner Name	
Attorney Docket No.	MEMC 98-3051 (2512.1)

Sheet	10	of	10
-------	----	----	----

A.M	129	VORONKOV, V., et al., "Grown-in microdefects, residual vacancies and oxygen precipitation banks in Czochralski silicon" Journal of Crystal Growth, 304 (1999) pp. 462-474	
	130	WINKLER et al. "Improvement of the Gate Oxide Integrity by Modifying Crystal Pulling and its Impact on Device Failures" J. Electrochem. Soc., vol. 141, No. 5 (1994) pp. 1398-1401. (May 1994).	
	131	ZIMMERMAN al. "Vacancy Concentration Wafer Mapping in Silicon" J. Crystal Growth, vol. 129 (1993) pp. 582-592. (No Month).	
	132	International Search Report for Application No. PCT/US 99/19958, filed 08/31/99, 11 pages	

Examiner Signature	A.N.H. D. MAI	Date Considered	5/02/03
-----------------------	---------------	--------------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.